NSN 5962-01-434-7693

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-434-7693

1.5 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

End Application:

Agm130

Features Provided:

Electrically alterable and programmable and electrostatic sensitive and monolithic

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Complementary-metal oxide-semiconductor logic

Input Circuit Pattern:

22 input

Criticality Code Justification:

Cbbl

Case Outline Source And Designator:

D-9 mil-m-38510

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit-programmable array logic

Voltage Rating And Type Per Characteristic:

-5.0 volts total supply and 7.0 volts total supply

Time Rating Per Chacteristic:

15.00 nanoseconds access

Memory Device Type:

Pal

Special Features:

Altered item, make from p/n 5962-8984105la, microcircuit array logic, monolithic silicon; program in accordance with specification vg02l012; nha vg02l116; used on wgu-40/b

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.). And 81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

24 printed circuit

Specification Data:

67268-5962-89841 government standard

Shelf Life:

N/a

NSN 5962-01-434-7693

Memory Microcircuit - Page 2 of 2



Demilitarization:

Yes - demil/mli

Fiig:

A458a0